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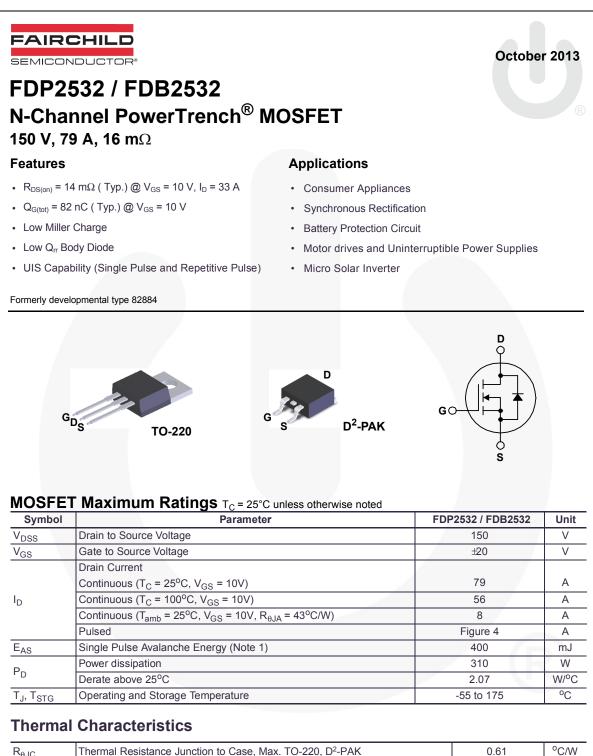


ON Semiconductor®

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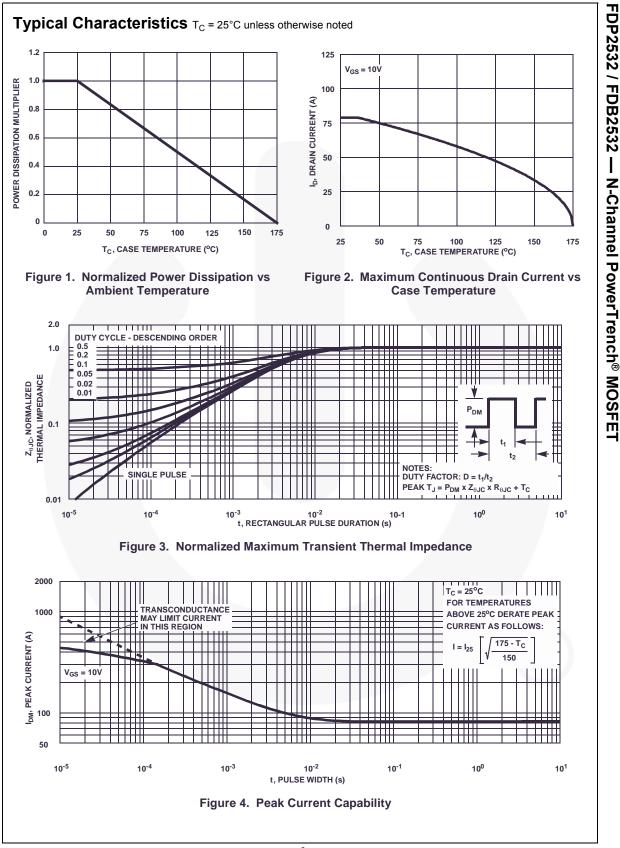
$R_{\theta JC}$	Thermal Resistance Junction to Case, Max. TO-220, D ² -PAK	0.61	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, Max. TO-220, D ² -PAK (Note 2)	62	°C/W
R_{\thetaJA}	Thermal Resistance Junction to Ambient D2-PAK, Max. 1in2 copper pad area	43	°C/W

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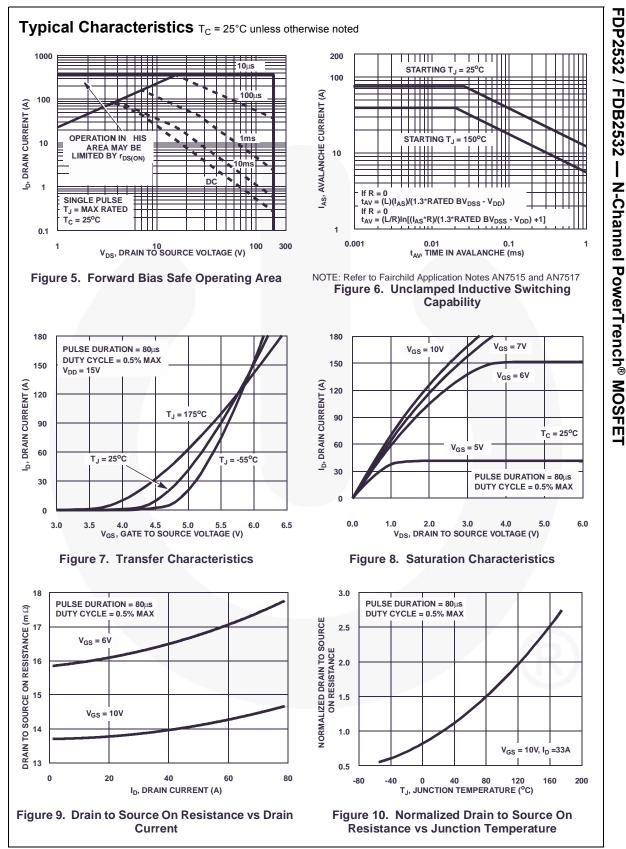
FDP2532 / FDB2532 — N-Channel PowerTrench[®] MOSFET

Device Marking FDB2532		Device Package Reel Size		Reel Size	Tape Width		Quantity	
		FDB2532	D ² -PAK	330 mm	24 mm		800 units	
FDP:	2532	FDP2532	TO-220	Tube	N/A		50 units	
Electric	al Char	acteristics T _c = 25°C	unless otherwis	se noted				
Symbol		Parameter	Test	Conditions	Min	Тур	Max	Unit
Off Chara	acteristic	S						
B _{VDSS}	Drain to S	ource Breakdown Voltage	I _D = 250μA	V _{GS} = 0V	150	-	-	V
I _{DSS}	Zero Gate	e Voltage Drain Current	V _{DS} = 120\		-	-	1	μA
	-		$V_{GS} = 0V$	$T_{\rm C} = 150^{\rm o}{\rm C}$	-	-	250	•
I _{GSS}	Gate to S	ource Leakage Current	V _{GS} = ±20V		-	-	±100	nA
On Chara	acteristic	6						
V _{GS(TH)}	Gate to S	ource Threshold Voltage		I _D = 250μA	2	-	4	V
			I _D = 33A, V		-	0.014	0.016	
r _{DS(ON)}	Drain to S	ource On Resistance	I _D = 16A, V		-	0.016	0.024	Ω
			I _D = 33A, V T _C = 175°C		-	0.040	0.048	
Dvnamic	Characte	eristics						
C _{ISS}	Input Cap				-	5870	-	pF
C _{OSS}	Output Ca	apacitance	V _{DS} = 25V, f = 1MHz	$V_{GS} = 0V,$	-	615	-	pF
C _{RSS}	Reverse 7	Transfer Capacitance			-	135	-	pF
Q _{g(TOT)}	Total Gate	e Charge at 10V	V _{GS} = 0V to	0 10V	-	82	107	nC
Q _{g(TH)}	Threshold	I Gate Charge	V _{GS} = 0V to	0 2V V _{DD} = 75V	-	11	14	nC
Q _{gs}	Gate to S	ource Gate Charge		I _D = 33A	-	23	-	nC
Q _{gs2}	Gate Cha	rge Threshold to Plateau		I _g = 1.0mA	-	13	-	nC
Q _{gd}	Gate to D	rain "Miller" Charge			-	19	-	nC
Resistive	Switchir	ng Characteristics (Va	_{GS} = 10V)					
t _{ON}	Turn-On T	īme			-	-	69	ns
t _{d(ON)}	Turn-On [Delay Time				16	- /	ns
t _r	Rise Time	9		$V_{DD} = 75V, I_D = 33A$ $V_{GS} = 10V, R_{GS} = 3.6\Omega$		30	-	ns
t _{d(OFF)}	Turn-Off	Delay Time	V _{GS} = 10V,			39	-	ns
t _f	Fall Time				-	17	-	ns
t _{OFF}	Turn-Off 1	īme			-	-	84	ns
Drain-So	urce Dioc	le Characteristics						
V _{SD}	Source to	Drain Diode Voltage	I _{SD} = 33A		-	-	1.25	V
30			I _{SD} = 16A		-	-	1.0	V
	Reverse I	Recovery Time	I _{SD} = 33A, dI _{SD} /dt= 100A/μs I _{SD} = 33A, dI _{SD} /dt= 100A/μs		-	-	105 327	ns
t _{rr} Q _{RR}	Devices	Recovery Charge			-	-		nC

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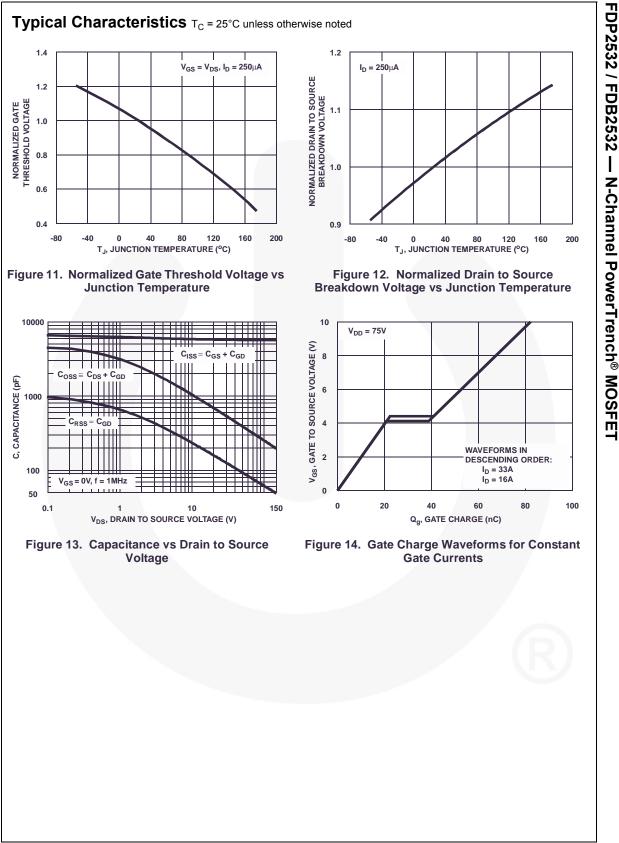


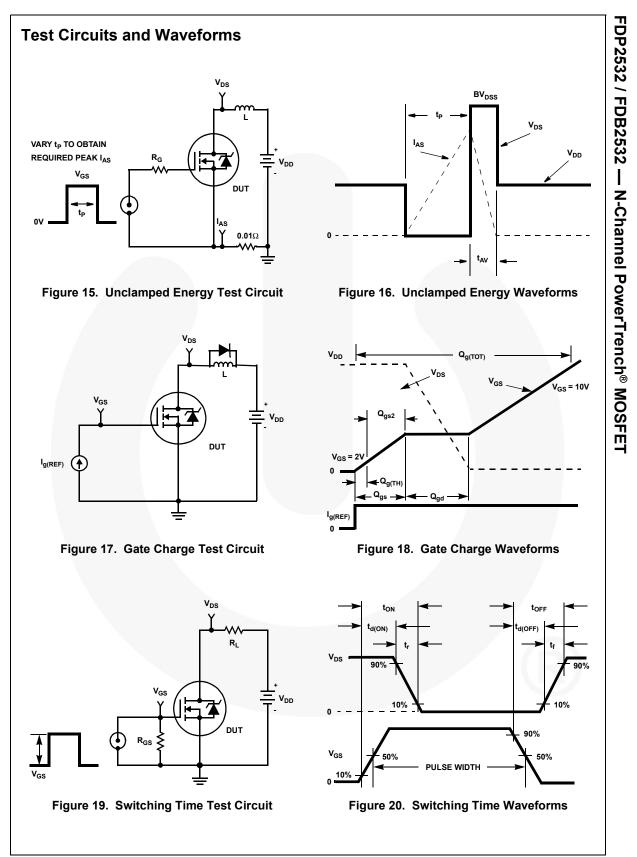
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Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A (°C), and thermal resistance $R_{\theta JA}$ (°C/W) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}}$$
(EQ. 1)

In using surface mount devices such as the TO-263 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

- Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
- 2. The number of copper layers and the thickness of the board.
- 3. The use of external heat sinks.
- 4. The use of thermal vias.
- 5. Air flow and board orientation.
- 6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the $R_{\theta,JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

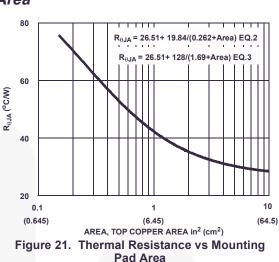
Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2 or 3. Equation 2 is used for copper area defined in inches square and equation 3 is for area in centimeters square. The area, in square inches or square centimeters is the top copper area including the gate and source pads.

$$R_{\Theta JA} = 26.51 + \frac{19.84}{(0.262 + Area)}$$
(EQ. 2)

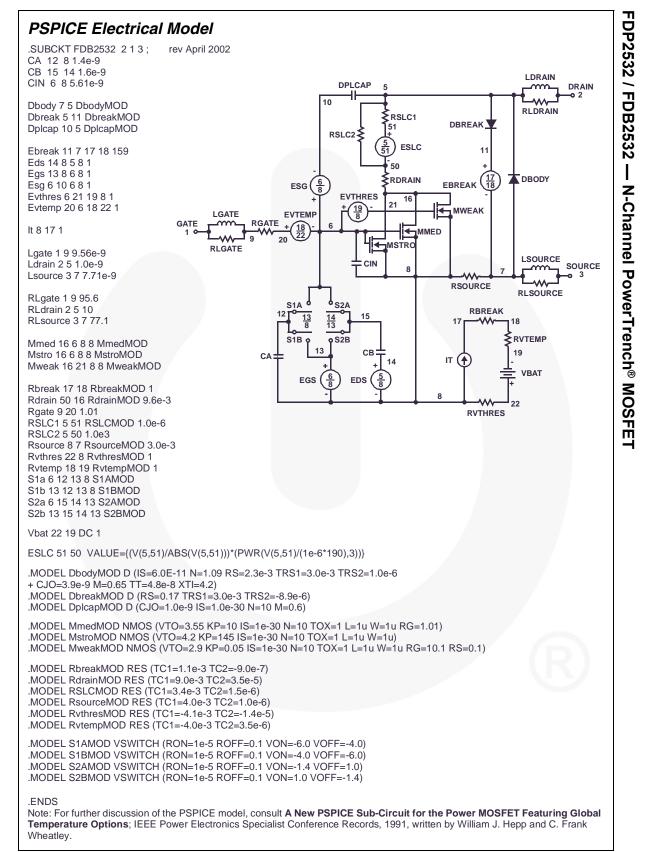
Area in Inches Squared

$$R_{\theta JA} = 26.51 + \frac{128}{(1.69 + Area)}$$
 (EQ. 3)

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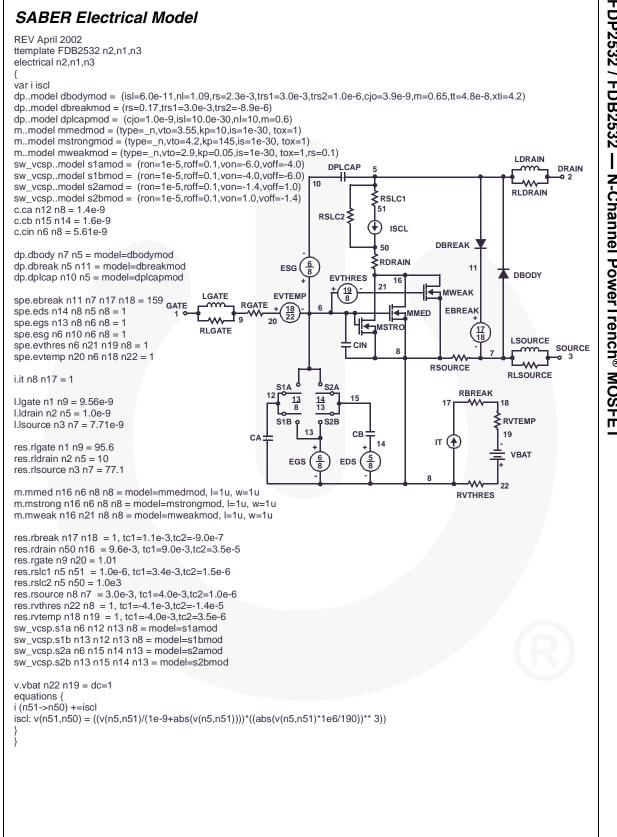


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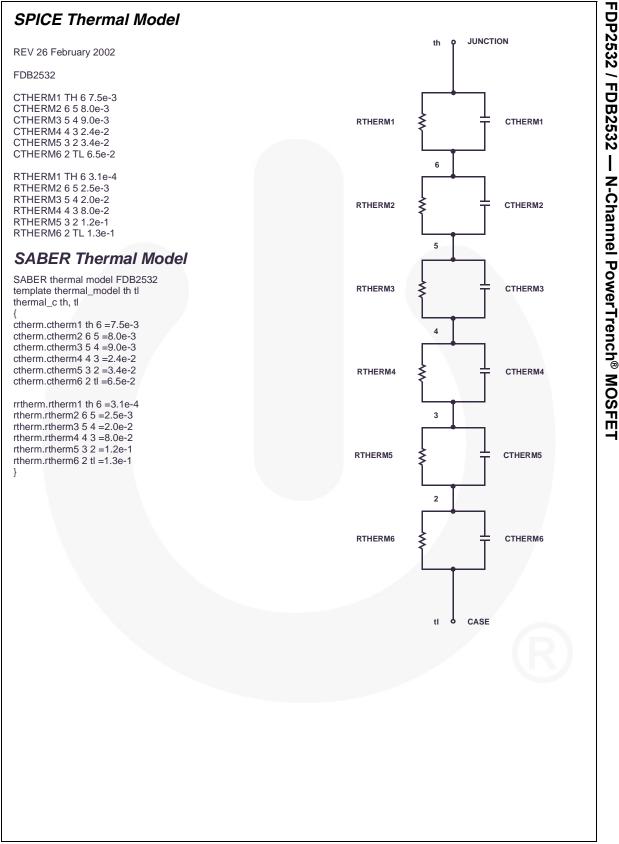


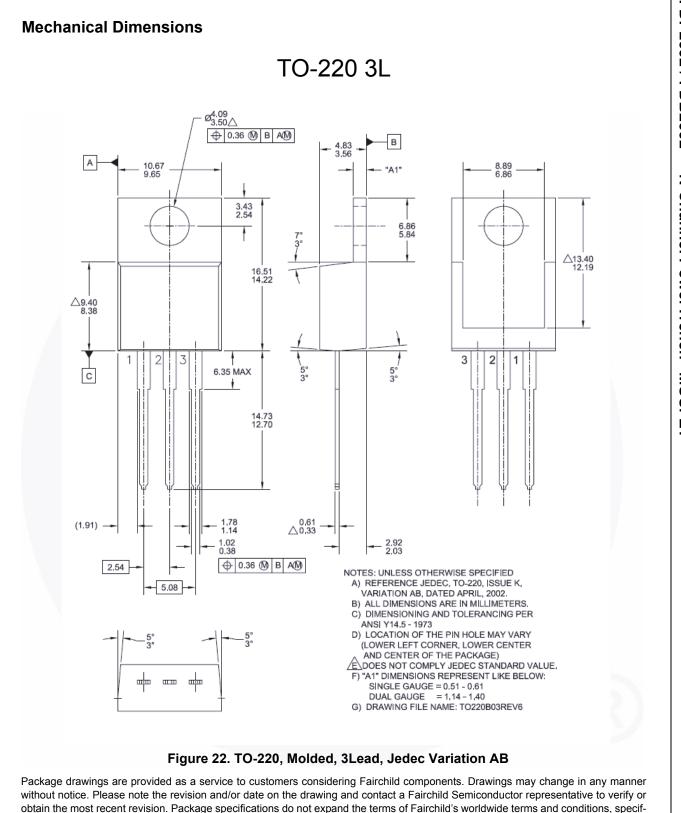
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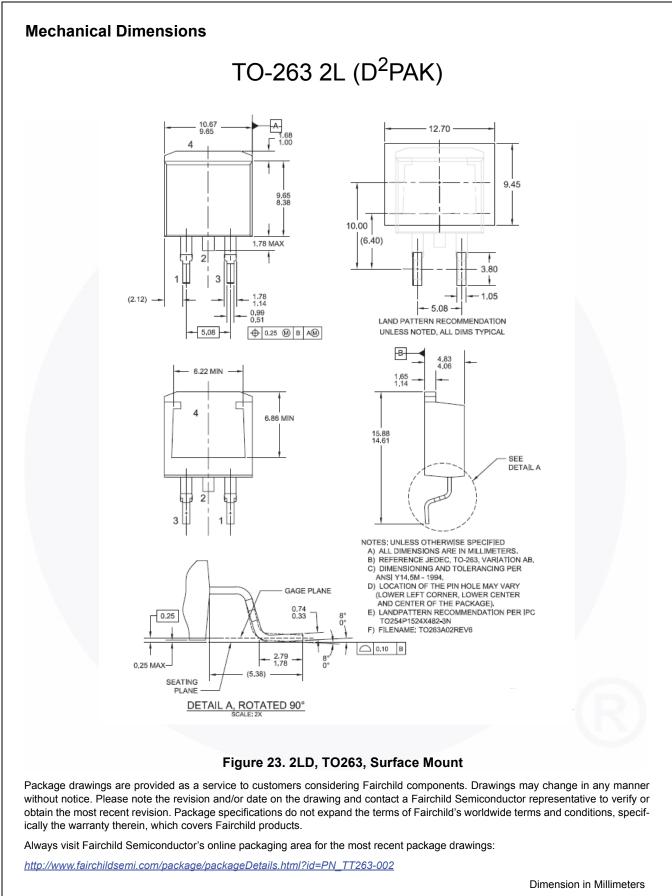


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Dimension in Millimeters





Not In Production

Obsolete

Rev. 166

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